

BYC10MX-650P Hyperfast power diode Rev.01 - 11 November 2022

#### **Product data sheet**

#### **1. General description**

Hyperfast power diode in a 2-lead TO220F plastic package.



#### 2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

#### 3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

#### 4. Quick reference data

able 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				650		V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>			10		А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_{\rm p}$ = 25 $\mu s;$ square-wave pulse		20			A
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		135			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			148		А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.50	2.30	V
Dynamic	characteristics		1				
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	13	-	ns

# **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	n.c.	mounting base; isolated		

# 6. Ordering information

Table 3. Ordering information									
Type number	Package	Orderable part number		Small packing	Package	Package			
	name		method	quantity	version	issue date			
BYC10MX-650P	TO220F-2L	BYC10MX-650PQ	Tube	50	TO220Fd-2L	02-Aug-2022			

## 7. Marking

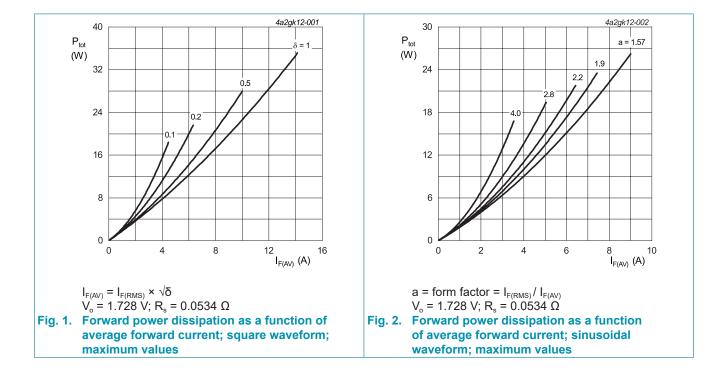
Table 4. Marking codes						
Type number	Marking codes					
BYC10MX-650P	BYC10MX 650P					

#### 8. Limiting values

#### Table 5. Limiting values

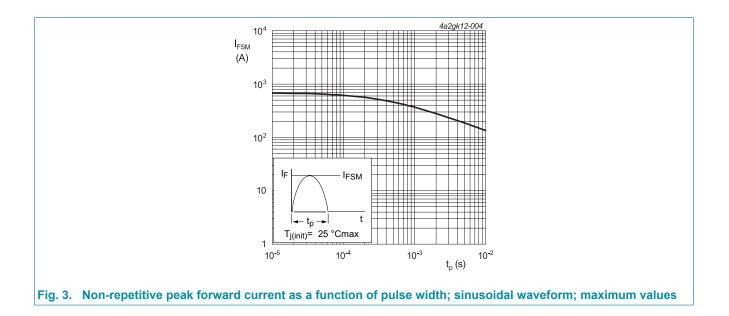
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2		10	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_{\rm p}$ = 25 $\mu s$ ; square-wave pulse		20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		135	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		148	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



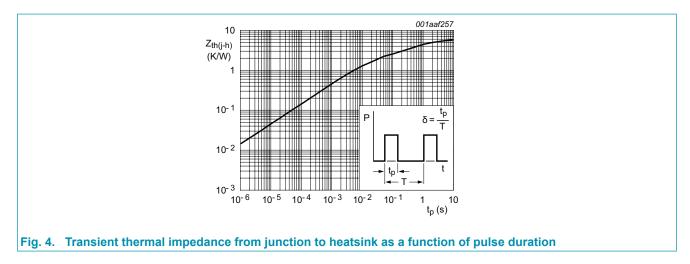
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### BYC10MX-650P Hyperfast power diode



## 9. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-h)}}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 4		-	-	4.8	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

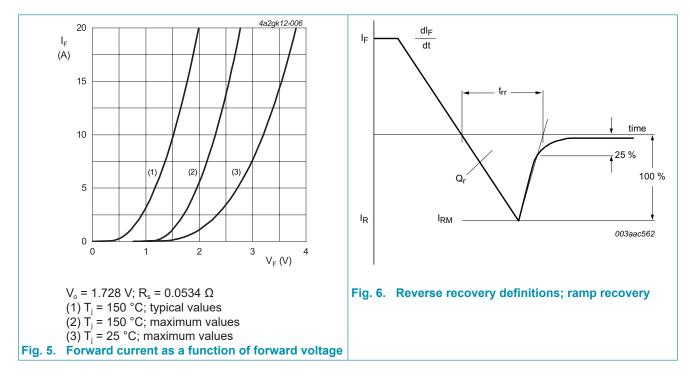


#### **10. Isolation characteristics**

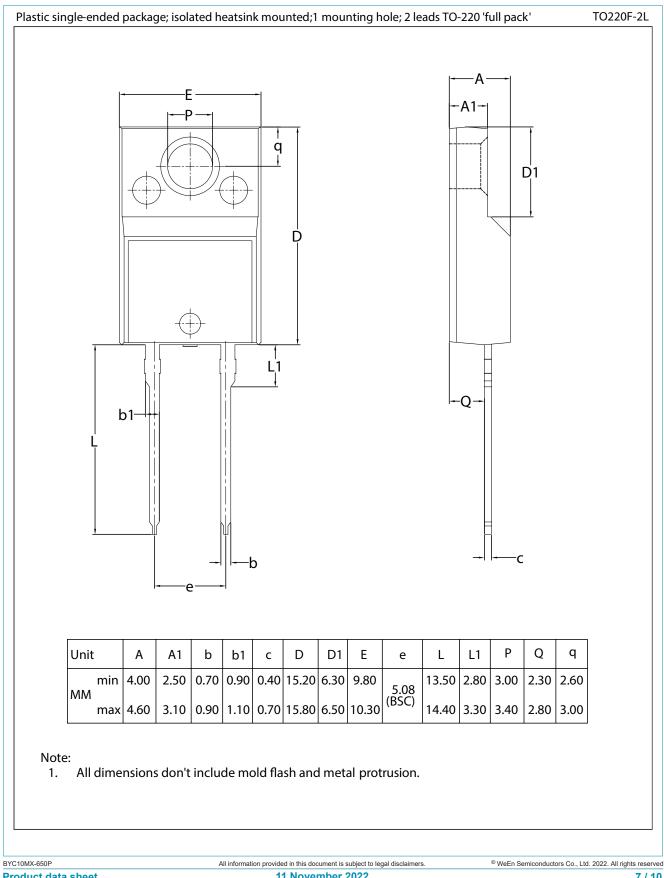
Table 7. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
$C_{\text{isol}}$	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

#### **11. Characteristics**

	haracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.50	2.30	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.5	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.1	0.8	mA
Dynamic	characteristics				Ċ		
Q <sub>r</sub> reverse charge	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$		-	37	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$		-	115	-	nC
t <sub>rr</sub> reverse	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 \text{ °C}$		-	20	-	ns
		I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>		-	13	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$		-	29	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$		-	48	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$		-	2.6	-	A
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$		-	4.8	-	A
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		10.8	-	-	mJ



## 12. Package outline



# BYC10MX-650P

#### Hyperfast power diode

## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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# BYC10MX-650P

#### 14. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Isolation characteristics	5
11. Characteristics	6
12. Package outline	7
13. Legal information	8
14. Contents	

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